

Abstracts

A low power 15 GHz frequency divider in a 0.8 /spl mu/m silicon bipolar production technology

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A low power static frequency divider with a divide ratio of 8 operating up to 15 GHz while consuming only 22 mA from a 3.6 V to 6 V supply is presented. It is manufactured in a conventional 0.8 /spl mu/m silicon bipolar technology with a cut-off frequency of 25 GHz. The chip is mounted in a SOT363 package.

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